

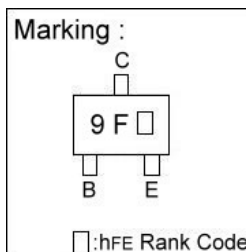
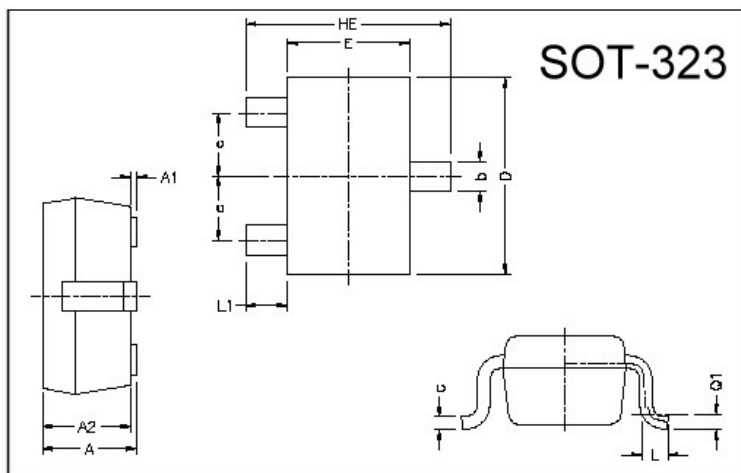
GSBC807

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GSBC807 is designed for switching and AF amplifier application, suitable for driver storages and low power output storages.

Package Dimensions



| REF. | Millimeter | | REF. | Millimeter | |
|------|------------|------|------|------------|------|
| | Min. | Max. | | Min. | Max. |
| A | 0.80 | 1.10 | L1 | 0.42 | REF. |
| A1 | 0 | 0.10 | L | 0.15 | 0.35 |
| A2 | 0.80 | 1.00 | b | 0.25 | 0.40 |
| D | 1.80 | 2.20 | c | 0.10 | 0.25 |
| E | 1.15 | 1.35 | e | 0.65 REF. | |
| HE | 1.80 | 2.40 | Q1 | 0.15 BSC. | |

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Ratings | Unit |
|------------------------------|------------------|------------|------|
| Junction Temperature | T _j | +150 | °C |
| Storage Temperature | T _{stg} | -55 ~ +150 | °C |
| Collector to Base Voltage | VCBO | -50 | V |
| Collector to Emitter Voltage | VCEO | -45 | V |
| Emitter to Base Voltage | VEBO | -5 | V |
| Collector Current | I _C | 800 | mA |
| Total Power Dissipation | PD | 225 | mW |

Characteristics at Ta = 25°C

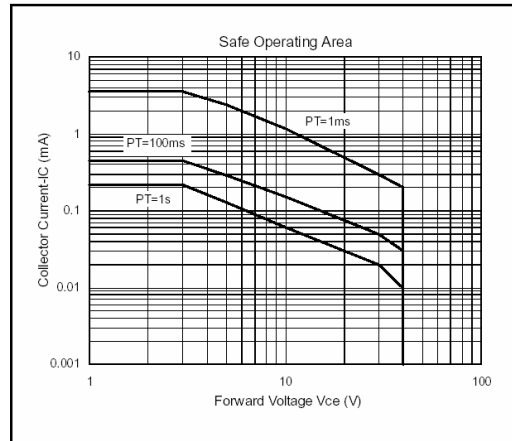
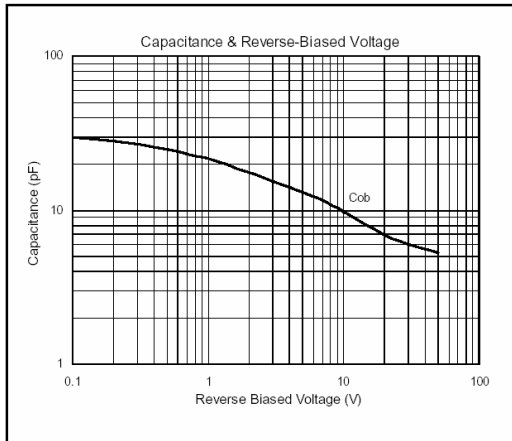
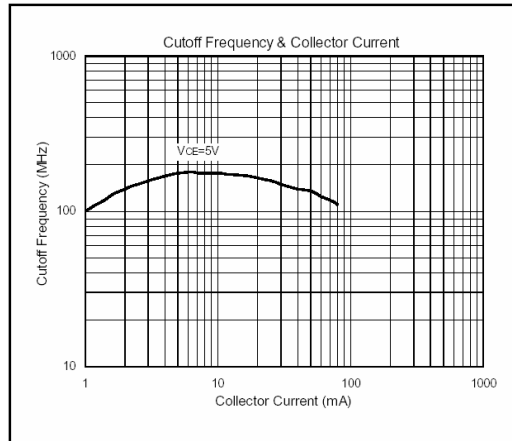
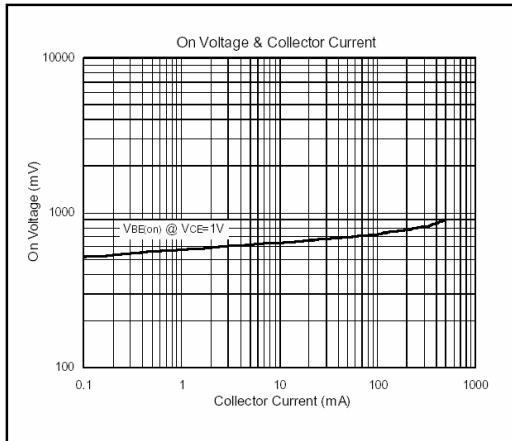
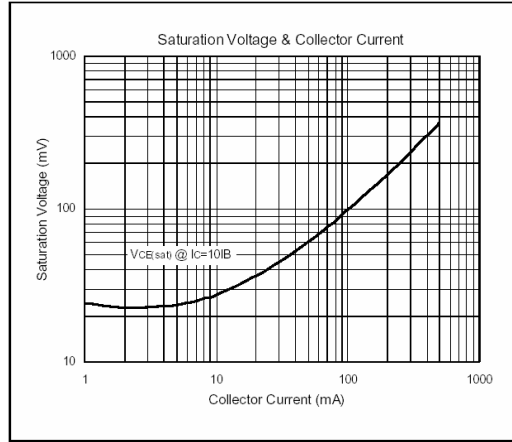
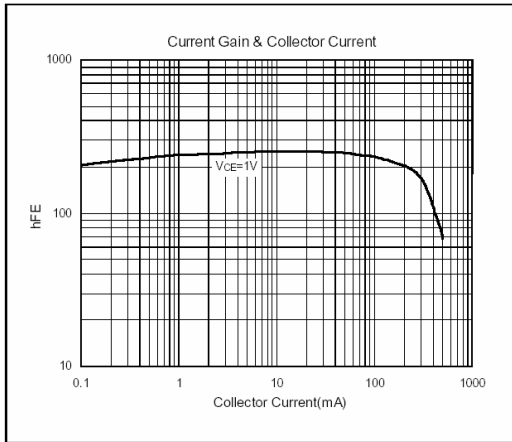
| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-----------------------|------|------|------|------|---|
| BVCBO | -50 | - | - | V | I _C =-100uA |
| BVCEO | -45 | - | - | V | I _C =-10mA |
| BVCES | -50 | - | - | V | I _C =-100uA |
| BVEBO | -5 | - | - | V | I _E =-100uA |
| ICES | - | - | -100 | nA | V _{CE} =-25V |
| IEBO | - | - | -100 | nA | V _{EB} =-4V |
| *V _{CE(sat)} | - | - | -700 | mV | I _C =-500mA, I _B =-50mA |
| *V _{BE(on)} | - | - | -1.2 | V | V _{CE} =-1V, I _C =-300mA |
| *h _{FE} | 100 | - | 630 | | V _{CE} =-1V, I _C =-100mA |
| f _T | - | 100 | - | MHz | V _{CE} =-5V, I _C =-10mA, f=100MHz |
| C _{ob} | - | - | 12 | pF | V _{CB} =-10V, f=1MHz, I _E =0A |

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Classification Of hFE

| Rank | 9FA | 9FB | 9FC |
|-------|-----------|-----------|-----------|
| Range | 100 - 250 | 160 - 400 | 250 - 630 |

Characteristics Curve



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